

Silicon NPN Power Transistors

2SC4106

DESCRIPTION

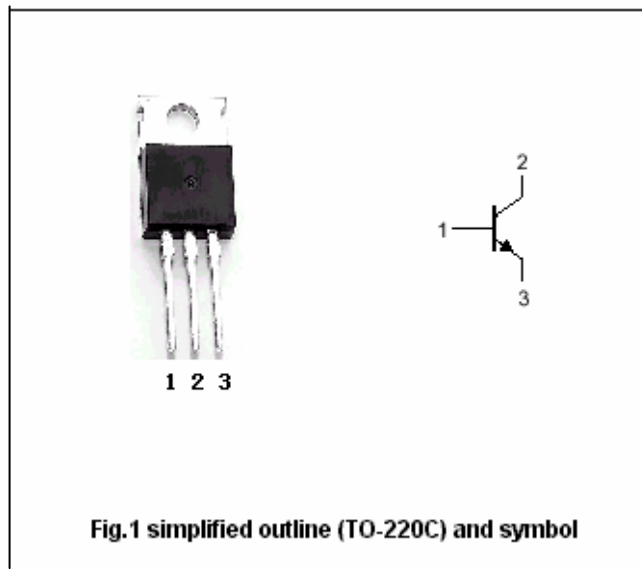
- With TO-220C package
- High breakdown voltage and high reliability
- Fast switching speed.
- Wide area of safe operation

APPLICATIONS

- 400V/7A switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current		3	A
P_C	Collector dissipation	$T_a=25^{\circ}\text{C}$	1.75	W
		$T_C=25^{\circ}\text{C}$	50	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA$; $R_{BE}=\infty$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			0.8	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=0.8A$; $V_{CE}=5V$	15		50	
h_{FE-2}	DC current gain	$I_C=4A$; $V_{CE}=5V$	10			
h_{FE-3}	DC current gain	$I_C=10mA$; $V_{CE}=5V$	10			
f_T	Transition frequency	$I_C=0.8A$; $V_{CE}=10V$		20		MHz
C_{OB}	Collector output capacitance	$f=1MHz$; $V_{CB}=10V$		80		pF

Switching times

t_{on}	Turn-on time	$I_C=5A$; $I_{B1}=1A$; $I_{B2}=-2A$; $R_L=40\Omega$ $V_{CC}=200V$			0.5	μs
t_{stg}	Storage time				2.5	μs
t_f	Fall time				0.3	μs

◆ h_{FE-1} classifications

L	M	N
15-30	20-40	30-50

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PACKAGE OUTLINE

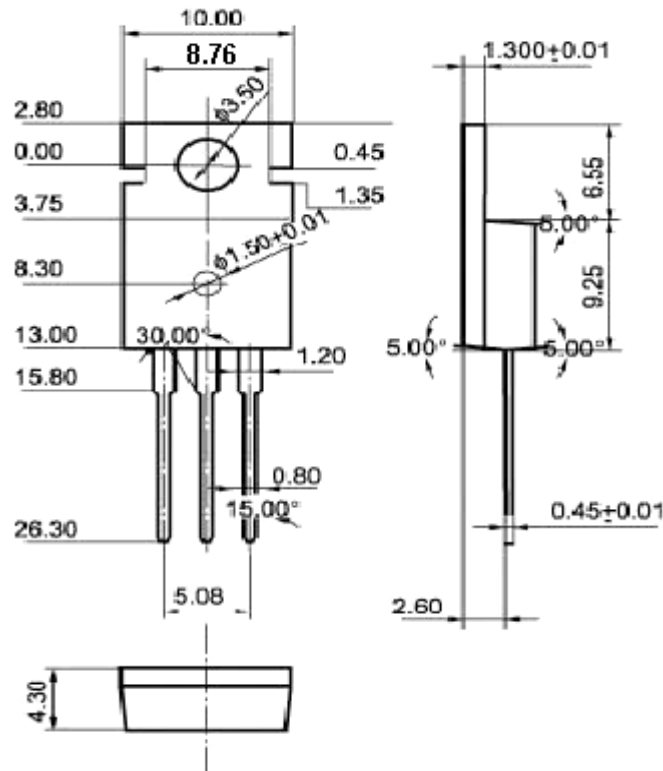


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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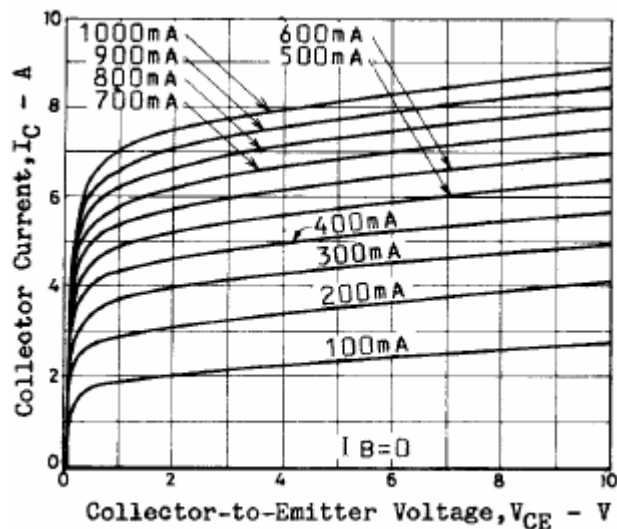


Fig.3 Static Characteristic

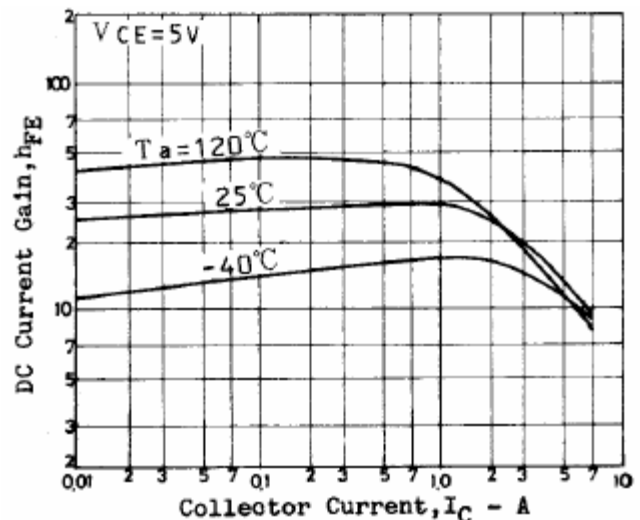


Fig.4 DC current Gain

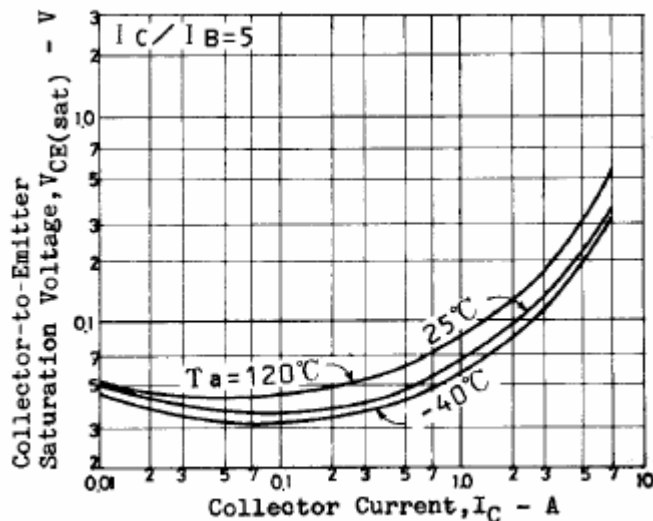


Fig.5 Collector-Emitter Saturation Voltage

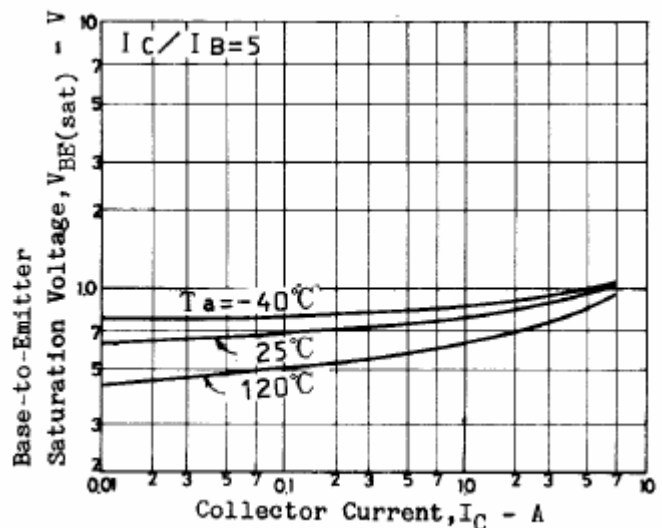


Fig.6 Base-Emitter Saturation Voltage

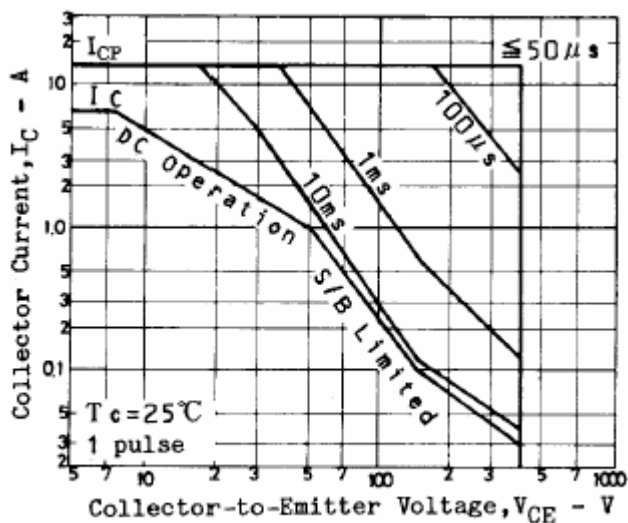


Fig.7 Safe Operating Area